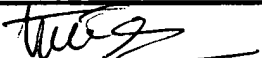


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		First Named Inventor	Philbert F. Marsh et al.
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OTHER PRIOR ART–NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume–issue number(s), publisher, city and/or country where published.	T ²
TT		ENOKI ET AL.; "Design and Characteristics of InGaAs/InP Composite-Channel HEFT's;" IEEE Transactions on Electron Devices, Vol. 42, No. 8, August 1995; 0018-9383/95; pages 413-418.	
TT		HOKE ET AL.; "Molecular Beam Epitaxial Growth and Device Performance of Metamorphic High Electron Mobility Transistor Structures Fabricated on GaAs Substrates;" J. Vac. Sci. Technol. B 17(3), May/June 1999; American Vacuum Society; 0734-211X/99/71(3)/1131/5; pages 1131-1135.	
TT		WHELAN ET AL.; "GaAs Metamorphic HEMT (MHEMT): An Attractive Alternative to InP HEMTs for High Performance Low Noise and Power Applications;" 2000 IEEE 0-7803-6320-5-00; pages 337-340.	
TT		deALAMO ET AL.; "Breakdown in Millimeter-Wave Power InP HEMT's: A Comparison with GaAs PHEMT's;" IEEE Journal of Solid-State Circuits, Vol. 34, No. 9, September 1999; 0018-9200/99; pages 1204-21.	

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